IN THE CLAIMS:

12. *(currently amended)* A hybrid active electronic and optical circuit integrated within a Silicon-On-Insulator (SOI) wafer, the SOI wafer including an insulator layer and an upper silicon layer having a thickness of less than 3μm, the hybrid active electronic and optical circuit comprising:

a relatively narrow waveguide located within the upper silicon layer of the SOI wafer for supporting the propagation of light, said relatively narrow waveguide having a thickness of less than 3 μm;

an active electronic circuit positioned proximate the waveguide, wherein a flow of light through the waveguide can be altered depending on a property of the active electronic circuit;

a light deflector at least partially located in the upper silicon layer, the light deflector is configured to deflect light impinging at the suitable incident angle to a suitable mode angle where light deflected by the light deflector enters the relatively narrow waveguide; and

an evanescent coupling region at least partially located within the upper silicon layer, the evanescent coupling region including a gap region positioned between the light deflector and the relatively narrow waveguide for optically ~~couples~~ coupling the deflected light ~~coupling portion~~ into the waveguide, such that light emitted from the light deflector ~~coupling portion~~ can pass via the evanescent coupling gap region to the relatively narrow waveguide at a suitable mode angle~~; and~~

~~a light deflector at least partially located in the upper silicon layer, the light deflector is configured to deflect light impinging at the suitable incident angle to a suitable mode angle where light deflected by the light deflector enters the waveguide~~.

13. – 14. *cancelled*

15. *(currently amended)* The hybrid active electronic and optical circuit of claim 12, wherein the evanescent coupling gap region includes a substantially constant thickness gap portion.

16. *(currently amended)* The hybrid active electronic and optical circuit of claim 12, wherein the evanescent coupling gap region ~~is at least partially formed using an optically clear adhesive~~ includes a tapered gap portion.

17. ***cancelled***

18. *(original)* The hybrid active electronic and optical circuit of claim 12, further including at least one optical device, wherein altering an electric voltage applied to the active electronic circuit affects a free carrier distribution in a region of the at least one optical device, and thereby changes an effective mode index of the at least one optical device.

19. ***cancelled***.

20. *(currently amended)* The hybrid active electronic and optical circuit of claim 12, wherein the evanescent coupling gap region has a thickness of less than 0.5μm.

21. – 28. ***cancelled***

29. *(original)* The hybrid active electronic and optical circuit of claim 12, wherein the hybrid active electronic and optical circuit includes a Fabry-Perot cavity.

30. *(original)* The hybrid active electronic and optical circuit of claim 12, wherein the hybrid active electronic and optical circuit includes a wavelength division multiplexer modulator.

31. *(original)* The hybrid active electronic and optical circuit of claim 12, wherein the hybrid active electronic and optical circuit includes a diode.

32. *(original)* The hybrid active electronic and optical circuit of claim 12, wherein the hybrid active electronic and optical circuit includes a transistor.

33. – 36. ***cancelled***

37. *(original)* The hybrid active electronic and optical circuit of claim 12, wherein the hybrid circuit includes one from the group of a p-n device, a field plated device, a Schottky device, a MOSCAP, and a MOSFET.

38. *(currently amended)* A hybrid active electronic and optical circuit integrated within a wafer, the water including an insulator layer and an upper silicon layer, the hybrid active electronic and optical circuit comprising:

a waveguide located within the upper silicon layer of the SOI wafer for supporting the propagation of light;

an active electronic circuit positioned proximate the waveguide, wherein a flow of light through the waveguide can be altered depending on a property of the active electronic circuit;

a light deflector at least partially located in the upper silicon layer, the light deflector configured to deflect light impinging at the suitable incident angle to a suitable mode angle where light deflected by the light deflector enters the relatively narrow waveguide; and

an evanescent coupling region at least partially located within the upper silicon layer, the evanescent coupling region including a gap region positioned between the light deflector and the relatively narrow waveguide for optically ~~couples~~ coupling the deflected light ~~coupling portion~~ into the waveguide, such that light emitted from the light deflector ~~coupling portion~~ can pass via the evanescent coupling gap region to the relatively narrow waveguide at a suitable mode angle~~; and~~

~~a light deflector at least partially located in the upper silicon layer, the light deflector is configured to deflect light impinging at the suitable incident angle to a suitable mode angle where light deflected by the light deflector enters the waveguide~~.

39. *(new)* The hybrid active electronic and optical circuit of claim 12, wherein the light deflector comprises an optical grating formed in the upper silicon layer.

40. *(new)* The hybrid active electronic and optical circuit of claim 12, wherein the light deflector comprises an optical prism formed in the upper silicon layer.

41. *(new)* The hybrid active electronic and optical circuit of claim 40 wherein the light deflector comprises regions of different effective mode indices to create a prism-like region in the upper silicon layer.

42. *(new)* The hybrid active electronic and optical circuit of claim 12, wherein the light deflector comprises an optical lens formed in the upper silicon layer.